Complementary Silicon Plastic Power Transistors

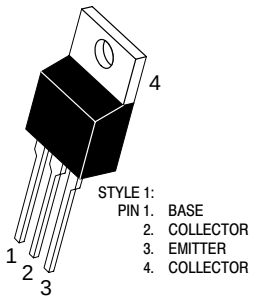
. . . designed for use in general–purpose amplifier and switching applications.

- DC Current Gain Specified to 10 Amperes
- High Current Gain — Bandwidth Product —
  f_T = 2.0 MHz (Min) @ I_C = 500 mAdc

PNP
MJE2955T*
NPN
MJE3055T*

*ON Semiconductor Preferred Device

10 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 60 VOLTS 75 WATTS



CASE 221A–09
TO–220AB

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	60	Vdc
Collector–Base Voltage	V_{CB}	70	Vdc
Emitter–Base Voltage	V_{EB}	5.0	Vdc
Collector Current	I_C	10	Adc
Base Current	I_B	6.0	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C MJE3055T, MJE2955T	P_D†	75 0.6	Watts W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θ_{JC}	1.67	°C/W

†Safe Area Curves are indicated by Figure 1. Both limits are applicable and must be observed.

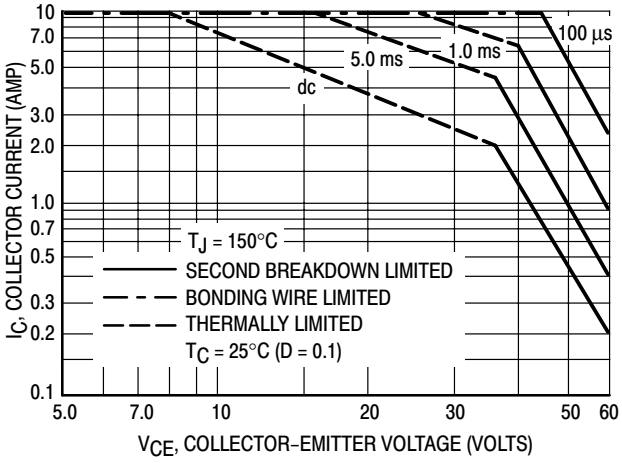


Figure 1. Active–Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on $T_{J(pk)}$ = 150°C. T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq$ 150°C. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown. (See AN415A)

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (1) (I_C = 200 mAdc, I_B = 0)	$V_{CEO(sus)}$	60	—	Vdc
Collector Cutoff Current (V_{CE} = 30 Vdc, I_B = 0)	I_{CEO}	—	700	μAdc
Collector Cutoff Current (V_{CE} = 70 Vdc, $V_{EB(off)}$ = 1.5 Vdc) (V_{CE} = 70 Vdc, $V_{EB(off)}$ = 1.5 Vdc, T_C = 150°C)	I_{CEX}	 — —	 1.0 5.0	mAdc
Collector Cutoff Current (V_{CB} = 70 Vdc, I_E = 0) (V_{CB} = 70 Vdc, I_E = 0, T_C = 150°C)	I_{CBO}	 — —	 1.0 10	mAdc
Emitter Cutoff Current (V_{BE} = 5.0 Vdc, I_C = 0)	I_{EBO}	—	5.0	mAdc
ON CHARACTERISTICS				
DC Current Gain (1) (I_C = 4.0 Adc, V_{CE} = 4 0 Vdc) (I_C = 10 Adc, V_{CE} = 4.0 Vdc)	h_{FE}	 20 5.0	 100 —	—
Collector–Emitter Saturation Voltage (1) (I_C = 4.0 Adc, I_B = 0.4 Adc) (I_C = 10 Adc, I_B = 3.3 Adc)	$V_{CE(sat)}$	 — —	 1.1 8.0	Vdc
Base–Emitter On Voltage (1) (I_C = 4.0 Adc, V_{CE} = 4.0 Vdc)	$V_{BE(on)}$	—	1.8	Vdc
DYNAMIC CHARACTERISTICS				
Current–Gain–Bandwidth Product (I_C = 500 mAdc, V_{CE} = 10 Vdc, f = 500 kHz)	f_T	2.0	—	MHz

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 20%.

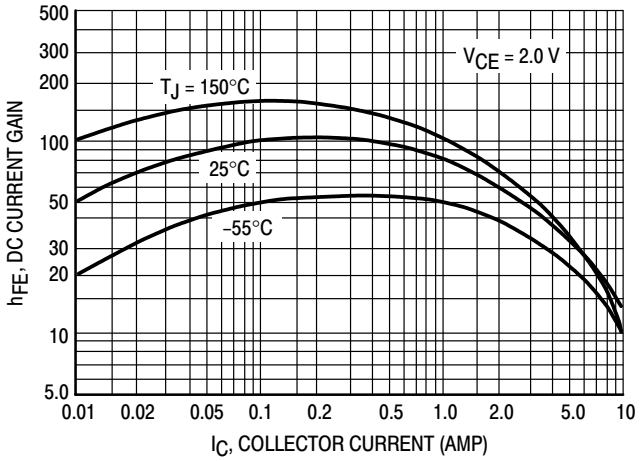


Figure 2. DC Current Gain

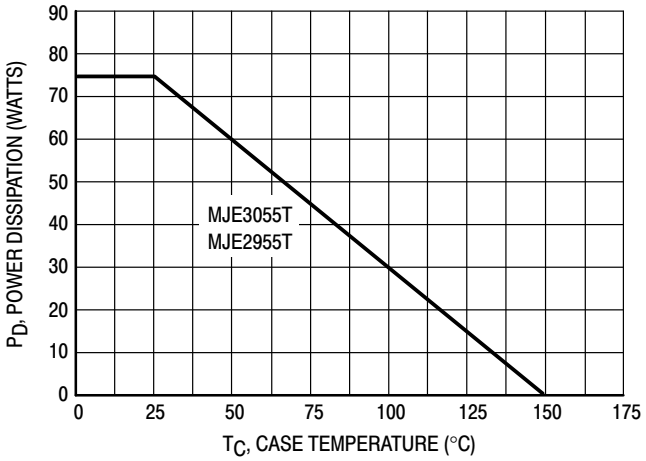
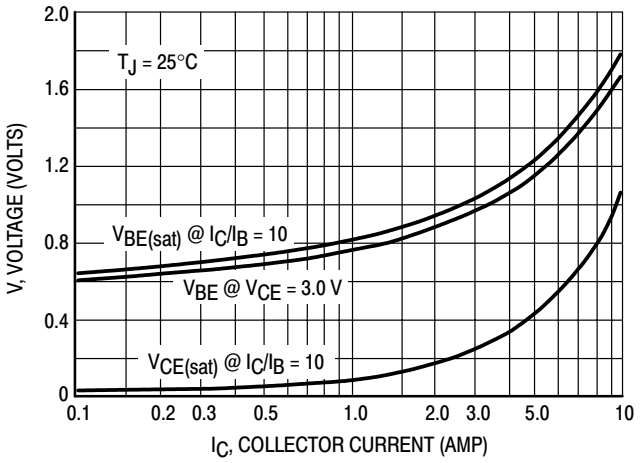


Figure 3. Power Derating

MJE2955T



MJE3055T

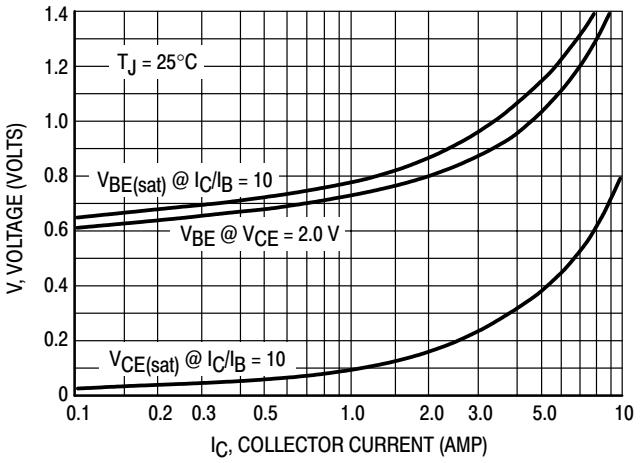
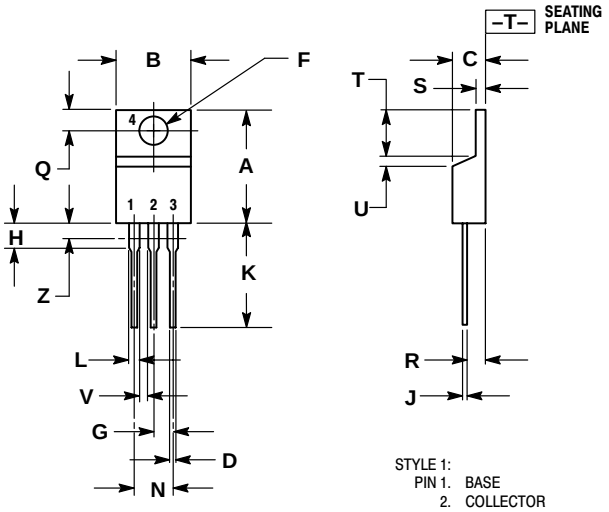


Figure 4. “On” Voltages

PACKAGE DIMENSIONS

TO–220AB
CASE 221A–09
ISSUE AA



STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

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Literature Fulfillment:
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